

Rev. A May.-2023



Schottky Barrier Diode in a TO-220 Plastic Package.



Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
RMS Voltage	V_{RMS}	70	V
DC Blocking Voltage	V_{DC}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	15	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	25	A
Peak Repetitive Forward Current	I_{FRM}	8	A
Repetitive Peak Reverse Surge Current	I_{RSM}	0.5	A
Thermal Resistance Junction to Case	$R_{\theta JA}$	12	/W
Junction Temperature Range	T_J	-55~175	
Storage Temperature Range	T_{STG}	-55~175	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=15A(T_J=25^\circ C)$			0.91	V
		$I_F=15A(T_J=125^\circ C)$			0.75	V
		$I_F=30A(T_J=25^\circ C)$			1.05	V
		$I_F=30A(T_J=125^\circ C)$			0.89	V
Instantaneous Reverse Current	I_R	$T_C=25$			0.05	mA
		$T_C=125$			20	mA

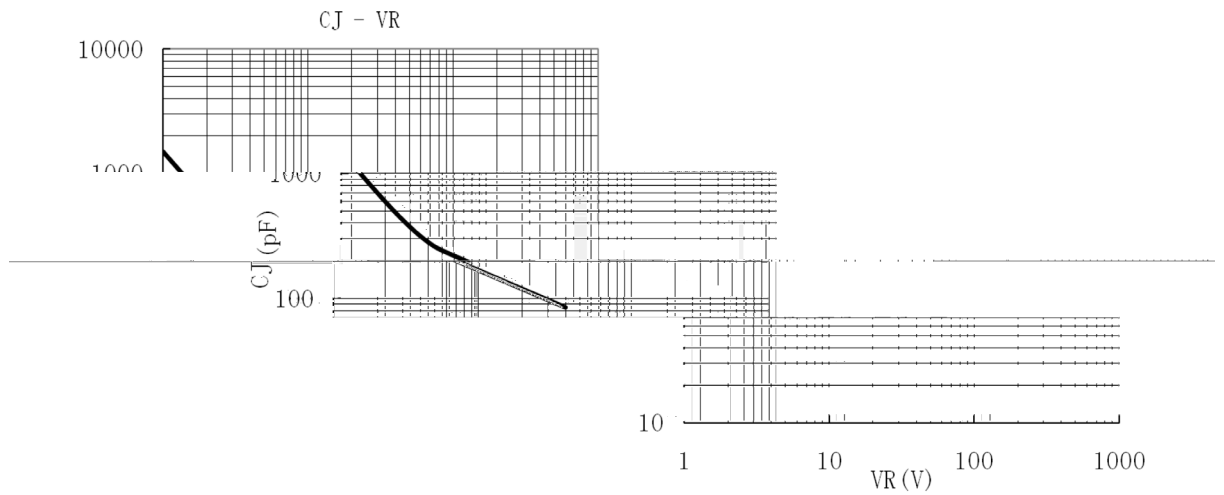
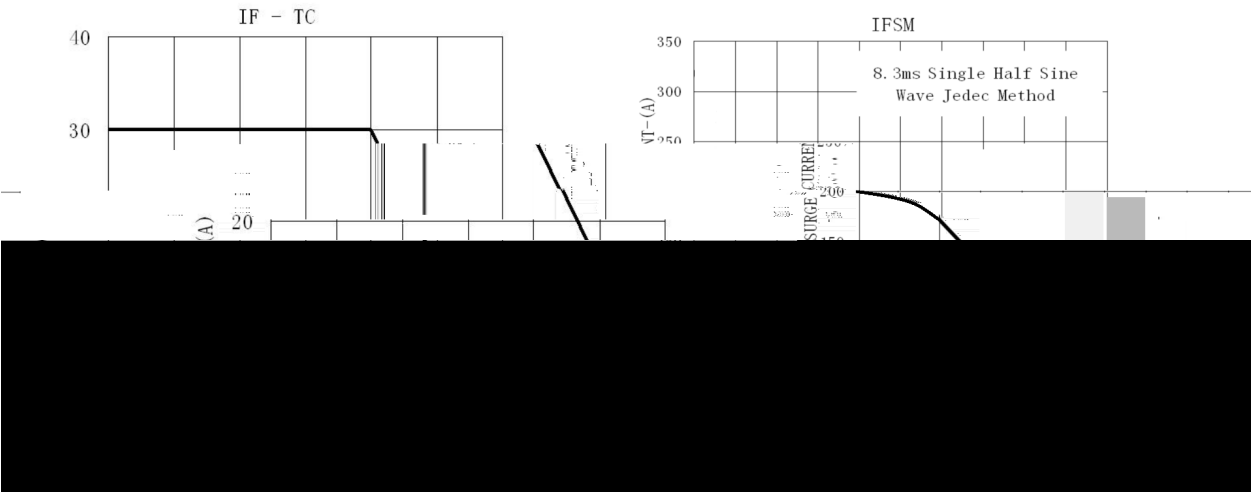
/Notes

 1.
 effect.

/Short duration pulse test used to minimize self-heating

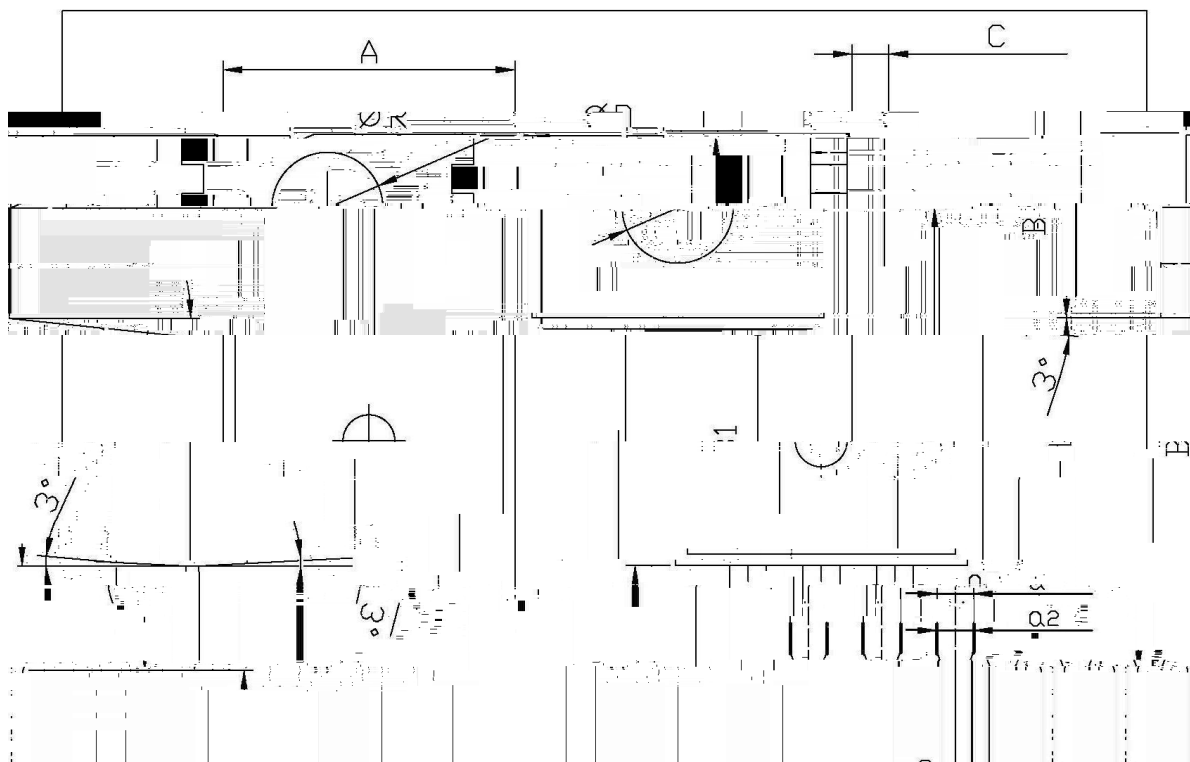
 2.
 single chip

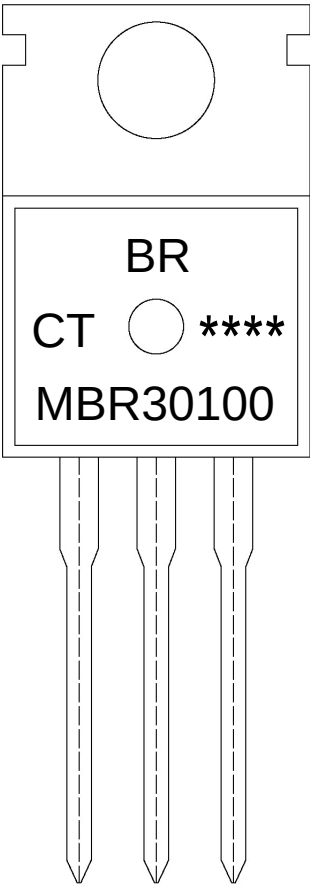
/ Unless otherwise noted, values for the parameters of a



TQ-220

单位: mm

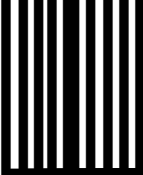




BR

Note:

BR:	Company Code
	Product Type
:	Internal Structure
****:	Lot No. Code, code change with Lot No



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